

1N4148

SWITCHING DIODES

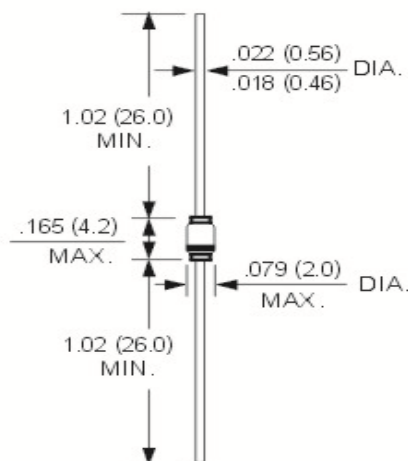


康比電子
HORNBY ELECTRONIC

Applications

- High-speed switching

DO-35



Dimensions in inches and (millimeters)

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

| Parameter | Symbol | Value | Unit |
|---|-------------|-------------------|------------------|
| Peak Reverse Voltage | V_{RM} | 100 | V |
| Reverse Voltage | V_R | 75 | V |
| Average Rectified Forward Current | $I_{F(AV)}$ | 150 | mA |
| Surge Forward Current at $t < 1\text{ s}$ | I_{FSM} | 500 | mA |
| Power Dissipation | P_{tot} | 500 ¹⁾ | mW |
| Junction Temperature | T_j | 200 | $^\circ\text{C}$ |
| Storage Temperature Range | T_{stg} | - 65 to + 200 | $^\circ\text{C}$ |

¹⁾ Valid provided that leads at a distance of 8 mm from case are kept at ambient temperature.

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

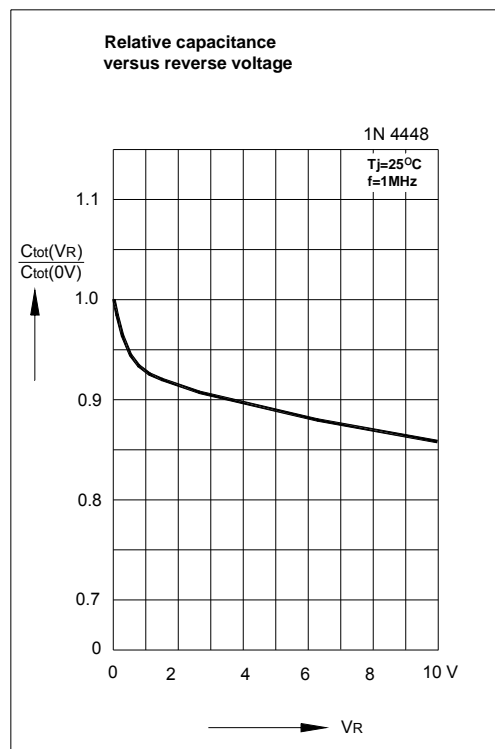
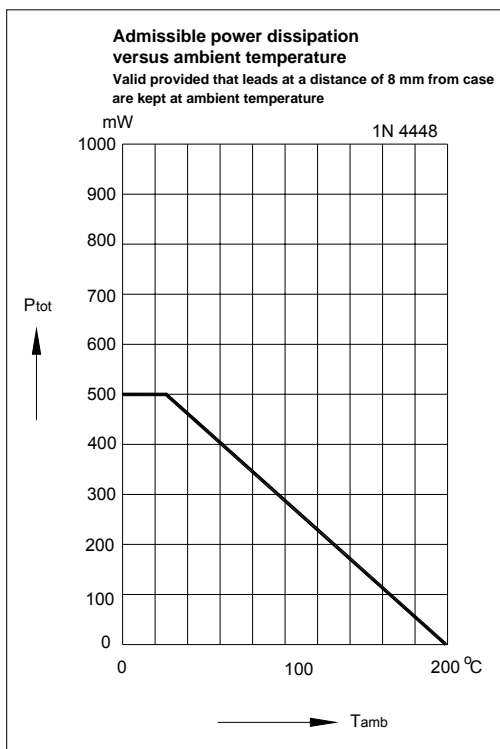
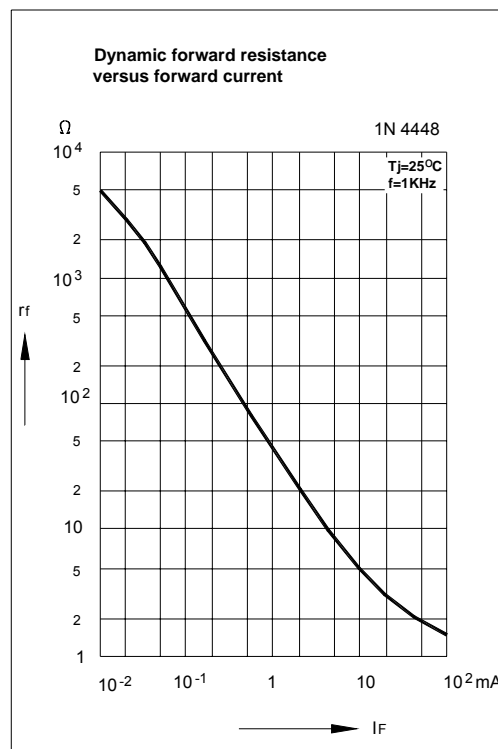
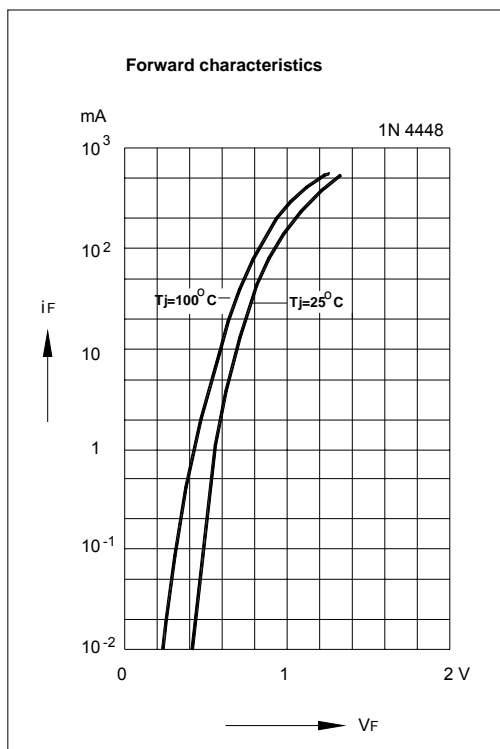
| Parameter | Symbol | Min. | Max. | Unit |
|---|-------------------------|-------------|---------------|--------------------------------------|
| Forward Voltage at $I_F = 5\text{ mA}$ at $I_F = 100\text{ mA}$ | V_F | 0.62 - | 0.72 1 | V |
| Reverse Leakage Current at $V_R = 20\text{ V}$ at $V_R = 75\text{ V}$ at $V_R = 20\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$ | I_R I_R I_R | - - - | 25 5 50 | nA μA μA |
| Reverse Breakdown Voltage at $I_R = 100\text{ }\mu\text{A}$ | $V_{(BR)R}$ | 100 | - | V |
| Capacitance at $V_R = 0$, $f = 1\text{ MHz}$ | C_{tot} | - | 4 | pF |
| Reverse Recovery Time at $I_F = 10\text{ mA}$ to $I_R = 1\text{ mA}$, $V_R = 6\text{ V}$, $R_L = 100\text{ }\Omega$ | t_{rr} | - | 4 | ns |

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